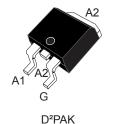
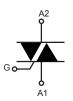


16 A - 800 V logic level T-series Triac in D2PAK









Product status link

T1610T-8G

Product summary		
I _{T(RMS)}	16 A	
V _{DRM} /V _{RRM}	800 V	
V _{DSM} /V _{RSM}	900 V	
I _{GT}	10 mA	

Features

- 150 °C maximum junction temperature
- Three quadrants
- · High commutation on resistive loads
- Surge capability V_{DSM}, V_{RSM} = 900 V
- · Benefits:
 - Easy direct control by MCU thanks to low 10 mA I_{GT}
 - Increase of thermal margin due to extended working T_i up to 150 °C

Applications

- · General purpose AC line load switching
- · Small home appliances with resistive loads
- Hybrid relays
- · Inrush current limiting circuits
- · Overvoltage crowbar protection

Description

The SMD T1610T-8G Triac can be used for the on/off or phase angle control function in general purpose AC switching with resistive loads. A Logic level T-series Triac, the T1610T-8G can be controlled directly from an MCU with a simplified circuit. T-series triacs are optimized for high EMI constraints.

The surface mount D²PAK package enables compact SMT designs for automated manufacturing.

D²PAK package's molding compound resin is halogen-free and meets UL94 flammability standard level V0.

Package environmentally friendly Ecopack2 graded (RoHS and Halogen Free compliance).



1 Characteristics

Table 1. Absolute maximum ratings (limiting values), T_j = 25 °C unless otherwise specified

Symbol	Parameter		Value	Unit
\/\/\/	Departitive peak off state valtage (FO GO LIP)	T _j = 125 °C	800	٧
V _{DRM} /V _{RRM}	Repetitive peak off-state voltage (50-60 Hz)	T _j = 150 °C	600	V
V _{DSM} /V _{RSM}	Non Repetitive peak off-state voltage	t _p = 10 ms, T _j = 25 °C	900	V
I _{T(RMS)}	RMS on-state current (full sine wave)	T _c = 126 °C	16	Α
I _{TSM} Non rep	Non repetitive surge peak on-state current (full cycle, T _j initial = 25	t = 16.7 ms	126	_
	°C	t = 20 ms	120	Α
I ² t	I ² t value for fusing	t _p = 10 ms	95	A ² s
dl/dt	Critical rate of rise of on-state current, $I_G = 2 \times I_{GT}$, $tr \le 100 \text{ ns}$	f = 100 Hz	100	A/µs
I _{GM}	Peak gate current		4	Α
V_{GM}	Peak Gate Voltage $t_p = 20 \mu s$, $T_j = 150 ^{\circ} C$		5	V
P _{G(AV)}	Average gate power dissipation $T_j = 150 ^{\circ}\text{C}$		1	W
T _{stg}	Storage junction temperature range	-40 to +150	°C	
Tj	Operating junction temperature range	-40 to +150	°C	

Table 2. Electrical characteristics (T_j = 25 °C, unless otherwise specified)

Symbol	Test conditions		Quadrants; T _j		Value	Unit
I _{GT} ⁽¹⁾	$V_D = 12 \text{ V}, R_L = 30 \Omega$		1 - 11 - 111	Max.	10	mA
V _{GT}	$V_D = 12 \text{ V}, R_L = 30 \Omega$		1 - 11 - 111	Max.	1.3	V
V _{GD}	V_D = 800 V, R_L = 3.3 k Ω	T _j = 125 °C	1 - 11 - 111	Min.	0.2	V
ı.	I _G = 1.2 x I _{GT}		1 - 111	Max.	20	mA
IL.	I _G = 1.2 x I _{GT}		II	Max.	30	mA
I _H ⁽²⁾	I _T = 500 mA, gate open		Max.	25	mA	
dV/dt (2)	V _D = 536 V, gate open		T _j = 125 °C	Min.	100	V/µs
av/at (=/	V _D = 402 V, gate open		T _j = 150 °C	Min.	50	V/µs
	$(dV/dt)c = 0.1 V/\mu s$		T _j = 125 °C	Min.	9	A/ms
(dl/dt)c (2)			T _j = 150 °C	IVIII I.	5.4	AVIIIS
(ui/ut)C (=/	$(dV/dt)c = 10 V/\mu s$		T _j = 125 °C	Min.	3	A/ms
			T _j = 150 °C	IVIIII.	1.8	

^{1.} Minimum I_{GT} is guaranteed at 5% of I_{GT} max

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^{2.} For both polarities of A2 referenced to A1.



Table 3. Static characteristics

Symbol	Test conditions	Tj		Value	Unit
V _{TM} ⁽¹⁾	I _T = 22.6 A, t _p = 380 μs	25 °C	Max.	1.55	V
V _{TO} ⁽¹⁾	Threshold on-state voltage	150 °C	Max.	0.85	V
R _D ⁽¹⁾	Dynamic resistance	150 °C	Max.	34	mΩ
I _{DRM} /I _{RRM}	V _{DRM} = V _{RRM} = 800 V	25 °C	Max.	5	μA
	VDRM - VRRM - 000 V	125°C	IVIAX.	1.0	mA
	V _{DRM} = V _{RRM} = 600 V	150 °C	Max.	3.6	mA

^{1.} For both polarities of A2 referenced to A1.

Table 4. Thermal resistance

Symbol	Parameter	Value	Unit		
R _{th(j-c)}	Junction to case (AC) D ² PAK		Max.	1.15	°C/W
R _{th(j-a)}	Junction to ambient (S _{CU} ⁽¹⁾ = 2 cm ²)	45	°C/W		

^{1.} Scu : copper pad surface under tab, 35 μm copper thickness on FR4 PCB.

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1.1 Characteristics (curves)

Figure 1. Maximum power dissipation versus on-state RMS current

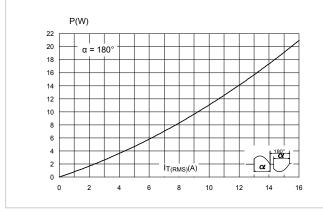


Figure 2. On-state RMS current versus case temperature

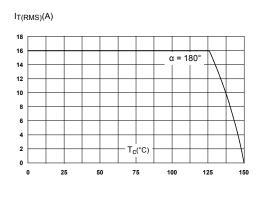


Figure 3. On-state RMS current versus ambient temperature (free air convection)

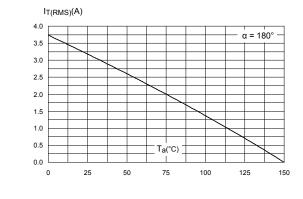


Figure 4. Relative variation of thermal impedance versus pulse duration

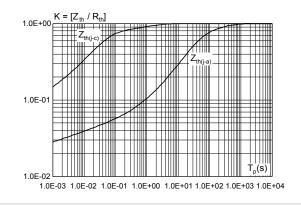


Figure 5. Relative variation of gate trigger voltage and current versus junction temperature (typical values)

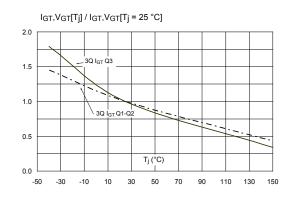
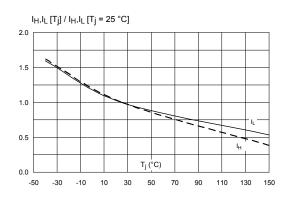


Figure 6. Relative variation of holding current and latching current versus junction temperature (typical values)



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Figure 7. Surge peak on-state current versus number of cycles

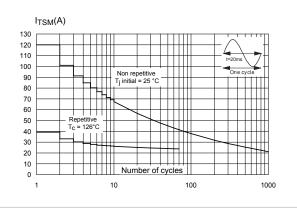


Figure 8. Non repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms

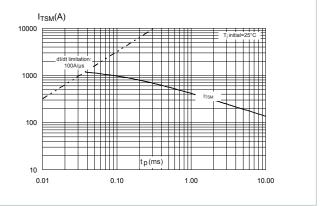


Figure 9. Relative variation of critical rate of decrease of main current versus junction temperature (typical values)

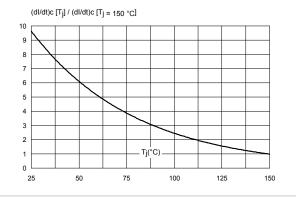


Figure 10. Relative variation of critical rate of decrease of main voltage versus junction temperature

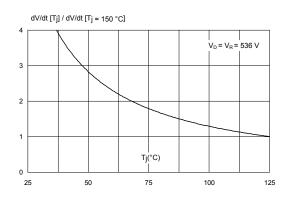


Figure 11. On-state characteristics (maximum values)

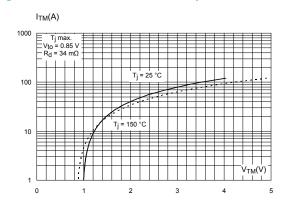
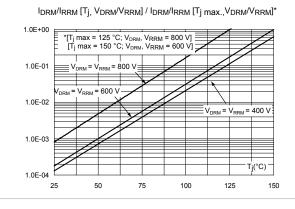


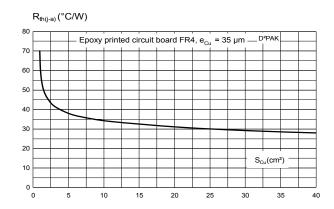
Figure 12. Relative variation of leakage current versus junction temperature for different values of blocking voltage



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Figure 13. Thermal resistance junction to ambient versus copper surface under tab



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2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 D²PAK package information

- ECOPACK2 compliant
- · Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL standard level V0

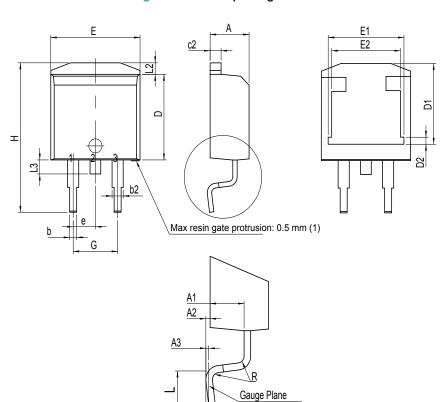


Figure 14. D²PAK package outline

(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

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Table 5. D²PAK package mechanical data

	Dimensions						
Ref.	Millimeters			Inches ⁽¹⁾			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.30		4.60	0.1693		0.1811	
A1	2.49		2.69	0.0980		0.1059	
A2	0.03		0.23	0.0012		0.0091	
A3		0.25			0.0098		
b	0.70		0.93	0.0276		0.0366	
b2	1.25		1.7	0.0492		0.0669	
С	0.45		0.60	0.0177		0.0236	
c2	1.21		1.36	0.0476		0.0535	
D	8.95		9.35	0.3524		0.3681	
D1	7.50		8.00	0.2953		0.3150	
D2	1.30		1.70	0.0512		0.0669	
е		2.54			0.1		
E	10.00		10.28	0.3937		0.4047	
E1	8.30		8.70	0.3268		0.3425	
E2	6.85		7.25	0.2697		0.2854	
G	4.88		5.28	0.1921		0.2079	
Н	15		15.85	0.5906		0.6240	
L	1.78		2.28	0.0701		0.0898	
L2	1.19		1.40	0.0468		0.0551	
L3	1.40		1.75	0.0551		0.0689	
R		0.40			0.0157		
V2 ⁽²⁾	0°		8°	0°		8°	

^{1.} Dimensions in inches are given for reference only

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^{2.} Degrees





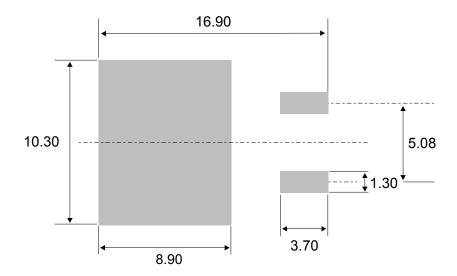
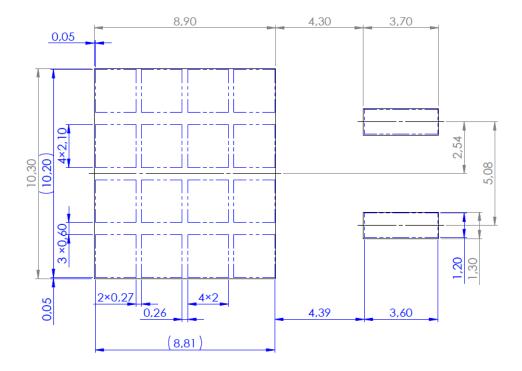


Figure 16. D²PAK stencil definitions(dimensions are in mm)



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3 Ordering information

Figure 17. Ordering information scheme

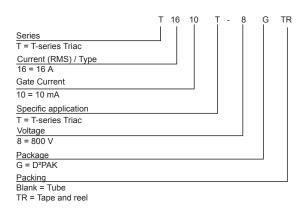


Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode	
T1610T-8G-TR	T1610T-8G	D2DAI/	D2DAK	160	1000	Tape and reel
T1610T-8G	110101-00	D²PAK	1.6 g	50	Tube	

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Revision history

Table 7. Document revision history

Date	Version	Changes
03-Apr-2018	1	Initial release.
17-Jul-2018	2	Updated Table 2. Electrical characteristics (T_j = 25 °C, unless otherwise specified).
29-Oct-2020	3	Updated Table 5 and added Figure 13. Thermal resistance junction to ambient versus copper surface under tab. Minor text changes.



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